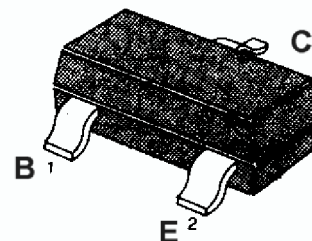


APPLICATION:High Frequency Low Noise Amplifier Application.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CE0}	15	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	50	mA
Collector Power Dissipation	P _c	100	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	28	100	198		V _{CE} = 5 V, I _c =1mA
Collector Cut-off Current	I _{CB0}			0.05	μA	V _{CB} = 12V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.05	μA	V _{EB} = 3 V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	30			V	I _c = 0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CE0}	15			V	I _c = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E = 0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.5	V	I _c = 10mA, I _B = 1 mA
Gain bandwidth product	f _T	700	1100		MHz	I _c = 5mA, V _{CE} = 5V
Common Base Output Capacitance	C _{ob}		1.3	1.7	PF	V _{CB} = 10V, I _E =0, f = 1 MHz

h_{FE} Classification And Marking

Print Mark	18D	18E	18F	18G	18H	18I
Classification	D	E	F	G	H	I
h _{FE}	28~45	39~60	54~80	72~108	97~146	132~198